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SCDS193D-AUGUST 2006-REVISED MARCH 2009

SPST CMOS ANALOG SWITCHES

FEATURES

• 2-V to 12-V Single-Supply Operation

JMENTS

- Specified ON-State Resistance:
 - 15 Ω Max With 12-V Supply
 - 20 Ω Max With 5-V Supply
 - 50 Ω Max With 3.3-V Supply
- Specified Low OFF-Leakage Currents:
 - 1 nA at 25°C
 - 10 nA at 85°C

- Specified Low ON-Leakage Currents:
 - 1 nA at 25°C
 - 10 nA at 85°C
- Low Charge Injection: 11.5 pC (12-V Supply)
- Fast Switching Speed:
 - $t_{ON} = 80 \text{ ns}, t_{OFF} = 50 \text{ ns} (12-V \text{ Supply})$
- Break-Before-Make Operation (t_{ON} > t_{OFF})
- TTL/CMOS-Logic Compatible With 5-V Supply

DESCRIPTION/ORDERING INFORMATION

The TS12A4514/TS12A4515 are single pole/single throw (SPST), low-voltage, single-supply CMOS analog switches, with very low switch ON-state resistance. The TS12A4514 is normally open (NO). The TS12A4515 is normally closed (NC).

These CMOS switches can operate continuously with a single supply between 2 V and 12 V. Each switch can handle rail-to-rail analog signals. The OFF-leakage current maximum is only 1 nA at 25°C or 10 nA at 85°C.

All digital inputs have 0.8-V to 2.4-V logic thresholds, ensuring TTL/CMOS-logic compatibility when using a 5-V supply.

For pin-compatible parts for use with dual supplies, see the TS12A4516/TS12A4517.

ORDERING INFORMATION

| T _A | PACKAG | 6E ⁽¹⁾⁽²⁾ | ORDERABLE PART NUMBER | TOP-SIDE MARKING(3) | |
|----------------|--------------------|----------------------|-----------------------|---------------------|--|
| PDIP – P | | Reel of 1000 | TS12A4514P | TS12A4514P | |
| | SOIC - D | Reel of 1500 | TS12A4514D | YD514 | |
| | 30IC - D | Reel of 2500 | TS12A4514DR | 10014 | |
| 40°C +- 05°C | SOP (SOT-23) - DBV | Reel of 3000 | TS12A4514DBVR | 9CJ_ | |
| –40°C to 85°C | PDIP – P | Reel of 1000 | TS12A4515P | TS12A4515P | |
| | SOIC - D | Reel of 1500 | TS12A4515D | VD545 | |
| | 30IC - D | Reel of 2500 | TS12A4515DR | YD515 | |
| | SOP (SOT-23) - DBV | Reel of 3000 | TS12A4515DBVR | 9CK_ | |

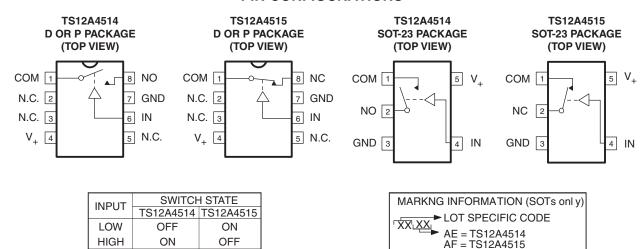
- (1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.
- (2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.
- (3) DBV: The last character designates assembly/test Site



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



PIN CONFIGURATIONS



N.C. - Not internally connected

NO - Normally open

NC - Normally closed

Absolute Minimum and Maximum Ratings(1)(2)

voltages referenced to GND

| | | | MIN | MAX | UNIT |
|-----------------------------|--|--|-------|-----------------------------------|------|
| V ₊ | Supply voltage range ⁽³⁾ | | -0.3 | 13 | V |
| V_{NC} V_{NO} V_{COM} | Analog voltage range ⁽⁴⁾ | | -0.3 | V ₊ + 0.3 or ±20 mA | V |
| | Continuous current into any terminal | | | ±20 | mA |
| | Peak current, NO or COM (pulsed at 1 ms, 1 | | ±30 | mA | |
| | ESD per method 3015.7 | | >2000 | V | |
| | | 8-pin plastic DIP (derate 9.09 mW/°C above 70°C) | | 727 | |
| | Continuous power dissipation (T _A = 70°C) | 8-pin SOIC (derate 5.88 mW/°C above 70°C) | | 471 | mW |
| | | 5-pin SOT-23 (derate 7.1 mW/°C above 70°C) | | 571 | |
| T _A | Operating temperature range | | -40 | 85 | °C |
| T _{stg} | Storage temperature range | | -65 | 150 | °C |
| | Lead temperature (soldering, 10 s) | | | 300 | °C |

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽³⁾ All voltages are with respect to ground, unless otherwise specified.

⁽⁴⁾ Voltages exceeding V₊ or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

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Electrical Characteristics for 5-V Supply⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $V_{INH} = 2.4 \text{ V}$, $V_{INL} = 0.8 \text{ V}$, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | T _A | MIN TYP(2) | MAX | UNIT | | |
|---------------------------------|-----------------------------------|---|----------------|------------|----------------|------|--|--|
| Analog Switch | | | I | , | | | | |
| Analog signal range | V_{COM}, V_{NO}, V_{NC} | | | 0 | V ₊ | V | | |
| ON state resistance | _ | $V_{+} = 4.5 \text{ V}, V_{COM} = 3.5 \text{ V},$ | 25°C | 9.5 | 15 | 0 | | |
| ON-state resistance | r _{on} | I _{COM} = 1 mA | Full | | 20 | Ω | | |
| ON-state resistance | _ | V _{COM} = 1 V, 2 V, 3 V, | 25°C | 1 | 3 | Ω | | |
| flatness | r _{on(flat)} | I _{COM} = 1 mA | Full | | 4 | 12 | | |
| NO, NC | I _{NO(OFF)} , | V ₊ = 5.5 V, V _{COM} = 1 V, | 25°C | | 1 | nA | | |
| OFF leakage current (3) | I _{NC(OFF)} | V_{NO} or $V_{NC} = 4.5 \text{ V}$ | Full | | 10 | ΠA | | |
| СОМ | 1 | V ₊ = 5.5 V, V _{COM} = 1 V, | 25°C | | 1 | ~ ^ | | |
| OFF leakage current (3) | I _{COM(OFF)} | V_{NO} or $V_{NC} = 4.5 \text{ V}$ | Full | | 10 | nA | | |
| СОМ | | V ₊ = 5.5 V, V _{COM} = 4.5 V, | 25°C | | 1 | A | | |
| ON leakage current (3) | I _{COM(ON)} | V_{NO} or $V_{NC} = 4.5 \text{ V}$ | Full | | 10 | nA | | |
| Digital Control Input (IN) | | · | | <u>.</u> | | | | |
| Input logic high | V _{IH} | | Full | 2.4 | V ₊ | V | | |
| Input logic low | V _{IL} | | Full | 0 | 0.8 | V | | |
| Input leakage current | I _{IH} , I _{IL} | V _{IN} = V ₊ , 0 V | Full | | 0.01 | μΑ | | |
| Dynamic | | · | I | , | | | | |
| Turn-on time | + | and Figure 2 | 25°C | 32 | 100 | | | |
| | t _{ON} | see Figure 2 | Full | | 125 | ns | | |
| Time off time | | Figure 0 | 25°C | 25 | 50 | | | |
| Turn-off time | t _{OFF} | see Figure 2 | Full | | 60 | ns | | |
| Charge injection ⁽⁴⁾ | Q_{C} | $C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega, \text{ See Figure 1}$ | 25°C | -3 | | рС | | |
| NO, NC OFF capacitance | $C_{NO(OFF)}$, $C_{NC(OFF)}$ | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF | | |
| COM OFF capacitance | $C_{COM(OFF)}$ | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF | | |
| COM ON capacitance | C _{COM(ON)} | f = 1 MHz, See Figure 4 | 25°C | 19 | | pF | | |
| Digital input capacitance | Cı | V _{IN} = V ₊ , 0 V | 25°C | 1.5 | | pF | | |
| Bandwidth | BW | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | 475 | | MHz | | |
| OFF isolation | O _{ISO} | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | -94 | | dB | | |
| Total harmonic distortion | THD | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | 0.08 | | % | | |
| Supply | | | | | | | | |
| V gunnhu gurrant | 1 | \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | 25°C | | 0.05 | | | |
| V ₊ supply current | I ₊ | $V_{IN} = 0 \text{ V or } V_+$ | Full | | 0.1 | μΑ | | |

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at $T_A = 25$ °C. Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested



Electrical Characteristics for 12-V Supply⁽¹⁾

 V_{+} = 11.4 V to 12.6 V, V_{INH} = 5 V, V_{INL} = 0.8 V, T_{A} = -40°C to 85°C (unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | T_A | MIN TYP ⁽²⁾ | MAX | UNIT |
|-----------------------------------|--|--|-------|------------------------|----------------|------|
| Analog Switch | | | | | | |
| Analog signal range | V_{COM}, V_{NO}, V_{NC} | | | 0 | V ₊ | V |
| ON state mediates as | | $V_{+} = 11.4 \text{ V}, V_{COM} = 10 \text{ V},$ | 25°C | 6.5 | 10 | 0 |
| ON-state resistance | r _{on} | I _{COM} = 1 mA | Full | | 15 | Ω |
| ON-state resistance | | V ₊ = 11.4 V, | 25°C | 1.5 | 3 | |
| flatness | r _{on(flat)} | $V_{COM} = 2 \text{ V}, 5 \text{ V}, 10 \text{ V},$ $I_{COM} = 1 \text{ mA}$ | Full | | 4 | Ω |
| NO, NC | I _{NO(OFF)} , | $V_{+} = 12.6 \text{ V}, V_{COM} = 1 \text{ V},$ | 25°C | | 1 | nA |
| OFF leakage current (3) | I _{NC(OFF)} | V_{NO} or $V_{NC} = 10 \text{ V}$ | Full | | 10 | ПА |
| СОМ | | V ₊ = 12.6 V, V _{COM} = 1 V, | 25°C | | 1 | ^ |
| OFF leakage current (3) | I _{COM(OFF)} | V_{NO} or $V_{NC} = 10 \text{ V}$ | Full | | 10 | nA |
| СОМ | | $V_{+} = 12.6 \text{ V}, V_{COM} = 10 \text{ V},$ | 25°C | | 1 | A |
| ON leakage current ⁽³⁾ | I _{COM(ON)} | $V_{+} = 12.6 \text{ V}, V_{COM} = 10 \text{ V}, V_{NO} \text{ or } V_{NC} = 10 \text{ V}$ | Full | | 10 | nA |
| Digital Control Input (IN) | | | | | | |
| Input logic high | V _{IH} | | Full | 5 | V ₊ | V |
| Input logic low | V _{IL} | | Full | 0 | 0.8 | V |
| Input leakage current | I _{IH} , I _{IL} | $V_{IN} = V_+, 0 V$ | Full | | 0.01 | μΑ |
| Dynamic | | | | | | • |
| Turn-on time | | | 25°C | 22 | 75 | |
| | t_{ON} | See Figure 2 | Full | | 80 | ns |
| | | | 25°C | 20 | 45 | |
| Turn-off time | t _{OFF} | See Figure 2 | Full | | 50 | ns |
| Charge injection ⁽⁴⁾ | Q_{C} | $C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega$, See Figure 1 | 25°C | -11.5 | | рС |
| NO, NC OFF capacitance | C _{NO(OFF)} C _{NC(OFF)} | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF |
| COM OFF capacitance | C _{COM(OFF)} | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF |
| COM ON capacitance | C _{COM(ON)} | f = 1 MHz, See Figure 4 | 25°C | 21.5 | | pF |
| Digital input capacitance | C _I | V _{IN} = V ₊ , 0 V | 25°C | 1.5 | | pF |
| Bandwidth | BW | $R_L = 50 \ \Omega, \ C_L = 15 \ pF, \ V_{NO} = 1 \ V_{RMS}, \ f = 100 \ kHz$ | 25°C | 520 | | MHz |
| OFF isolation | O _{ISO} | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | -95 | | dB |
| Total harmonic distortion | THD | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | 0.07 | | % |
| Supply | | <u> </u> | | | | |
| M. aumaha auma-at | | V 0.V == V | 25°C | | 0.05 | A |
| V ₊ supply current | I ₊ | $V_{IN} = 0 \text{ V or } V_+$ | Full | | 0.2 | μΑ |

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

 ⁽²⁾ Typical values are at T_A = 25°C.
 (3) Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested

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Electrical Characteristics for 3-V Supply⁽¹⁾

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | T _A | MIN TYP ⁽²⁾ | MAX | UNIT | |
|------------------------------------|-----------------------------|---|----------------|------------------------|----------------|-------|--|
| Analog Switch | | · · | | • | | | |
| Analog signal range | V_{COM}, V_{NO}, V_{NC} | | | 0 | V ₊ | V | |
| ON state registeres | _ | $V_{+} = 3 \text{ V}, V_{COM} = 1.5 \text{ V},$ | 25°C | 18.5 | 40 | 0 | |
| ON-state resistance | r _{on} | $I_{NO} = 1 \text{ mA},$ | Full | | 50 | Ω | |
| ON-state resistance | | V ₊ = 3 V, | 25°C | 1 | 3 | | |
| flatness | r _{on(flat)} | V _{COM} = 1 V, 1.5 V, 2 V, I _{COM} = 1 mA | Full | | 4 | Ω | |
| NO, NC | I _{NO(OFF)} , | $V_{+} = 3.6 \text{ V}, V_{COM} = 1 \text{ V},$ | 25°C | | 1 | nA | |
| OFF leakage current (3) | I _{NC(OFF)} | V_{NO} or $V_{NC} = 3 \text{ V}$ | Full | | 10 | ПА | |
| COM | I _{COM(OFF)} | $V_{+} = 3.6 \text{ V}, V_{COM} = 1 \text{ V},$ | 25°C | | 1 | nA | |
| OFF leakage current ⁽³⁾ | 'COM(OFF) | V_{NO} or $V_{NC} = 3 \text{ V}$ | Full | | 10 | 117 \ | |
| COM | I _{COM(ON)} | $V_{+} = 3.6 \text{ V}, V_{COM} = 3 \text{ V}, V_{NO} \text{ or } V_{NC} = 3 \text{ V}$ | 25°C | | 1 | nA | |
| ON leakage current ⁽³⁾ | ·COM(ON) | V_{NO} or $V_{NC} = 3 \text{ V}$ | Full | | 10 | .,, | |
| Digital Control Input (IN) | | | | | 1 | | |
| Input logic high | V_{IH} | | Full | 2.4 | V_{+} | V | |
| Input logic low | V_{IL} | | Full | 0 | 8.0 | V | |
| Input leakage current | I_{IH},I_{IL} | $V_{IN} = V_+, 0 V$ | Full | | 0.01 | μΑ | |
| Dynamic | | | | | | | |
| Turn-on time ⁽⁴⁾ | t _{ON} | See Figure 2 | 25°C | 63 | 120 | ns | |
| Turr-or time | ON | See Figure 2 | Full | | 175 | 113 | |
| Turn-off time ⁽⁴⁾ | t | See Figure 2 | 25°C | 33 | 80 | ns | |
| | t _{OFF} | Occ Figure 2 | Full | | 120 | 113 | |
| Charge injection ⁽⁴⁾ | Q_{C} | C _L = 1 nF, See Figure 1 | 25°C | -1.5 | | рC | |
| NO, NC OFF capacitance | $C_{NO(OFF)},\ C_{NC(OFF)}$ | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF | |
| COM OFF capacitance | C _{COM(OFF)} | f = 1 MHz, See Figure 4 | 25°C | 7.5 | | pF | |
| COM ON capacitance | C _{COM(ON)} | f = 1 MHz, See Figure 4 | 25°C | 17 | | pF | |
| Digital input capacitance | C _I | V _{IN} = V ₊ , 0 V | 25°C | 1.5 | | pF | |
| Bandwidth | BW | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | 460 | | MHz | |
| OFF isolation | O _{ISO} | $R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$ | 25°C | -94 | | dB | |
| Total harmonic distortion | THD | $R_L = 50 \ \Omega, \ C_L = 15 \ pF, \ V_{NO} = 1 \ V_{RMS}, \ f = 100 \ kHz$ | 25°C | 0.15 | | % | |
| Supply | | <u> </u> | | | ' | | |
| V cumply ourrest | 1 | \/ - 0 \/ or \/ | 25°C | | 0.03 | ^ | |
| V ₊ supply current | I ₊ | $V_{IN} = 0 \text{ V or } V_+$ | Full | | 0.05 | μΑ | |

The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at $T_A = 25$ °C. Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested



PIN DESCRIPTION(1)

| | PIN | I NO. | | | |
|---------|--------|---------|--------|----------------|--|
| TS12 | A4514 | TS12 | A4515 | NAME | DESCRIPTION |
| D, P | SOT-23 | D, P | SOT-23 | | |
| 1 | 1 | 1 | 1 | COM | Common |
| 2, 3, 5 | _ | 2, 3, 5 | - | N.C. | No connect (not internally connected) |
| 4 | 5 | 4 | 5 | V ₊ | Power supply |
| 6 | 4 | 6 | 4 | IN | Digital control to connect COM to NO or NC |
| 7 | 3 | 7 | 3 | GND | Digital ground |
| 8 | 2 | _ | _ | NO | Normally open |
| _ | _ | 8 | 2 | NC | Normally closed |

⁽¹⁾ NO, NC, and COM pins are identical and interchangeable. Any may be considered as an input or an output; signals pass in both directions.



APPLICATION INFORMATION

Power-Supply Considerations

The TS12A4514/TS12A4515 construction is typical of most CMOS analog switches, except that they have only two supply pins: V_+ and GND. V_+ and GND drive the internal CMOS switches and set their analog voltage limits. Reverse ESD-protection diodes are internally connected between each analog-signal pin and both V_+ and GND. One of these diodes conducts if any analog signal exceeds V_+ or GND.

Virtually all the analog leakage current comes from the ESD diodes to V_+ or GND. Although the ESD diodes on a given signal pin are identical and, therefore, fairly well balanced, they are reverse biased differently. Each is biased by either V_+ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V_+ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity.

There is no connection between the analog-signal paths and V_{+} or GND.

 V_+ and GND also power the internal logic and logic-level translators. The logic-level translators convert the logic levels to switched V_+ and GND signals to drive the analog signal gates.

Logic-Level Thresholds

The logic-level thresholds are CMOS/TTL compatible when V_+ is 5 V. As V_+ is raised, the level threshold increases slightly. When V_+ reaches 12 V, the level threshold is about 3 V – above the TTL-specified high-level minimum of 2.8 V, but still compatible with CMOS outputs.

CAUTION:

If the user is using the TS12A4514 or TS12A4515 with a V+ supply of 3 V, then the control input (IN) voltage should not exceed V+, otherwise the output levels can exceed 3 V and violate the absolute maximum rating, potentially damaging the device.

High-Frequency Performance

In $50-\Omega$ systems, signal response is reasonably flat up to 250 MHz (see *Typical Operating Characteristics*). Above 20 MHz, the on response has several minor peaks that are highly layout dependent. The problem is not in turning the switch on; it is turning it off. The OFF-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 10 MHz, OFF isolation is about -45 dB in $50-\Omega$ systems, decreasing (approximately 20 dB per decade) as frequency increases. Higher circuit impedances also make OFF isolation decrease. OFF isolation is about 3 dB above that of a bare IC socket, and is due entirely to capacitive coupling.

Test Circuits/Timing Diagrams

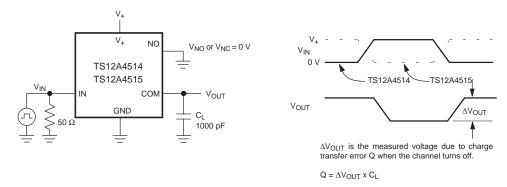


Figure 1. Charge Injection



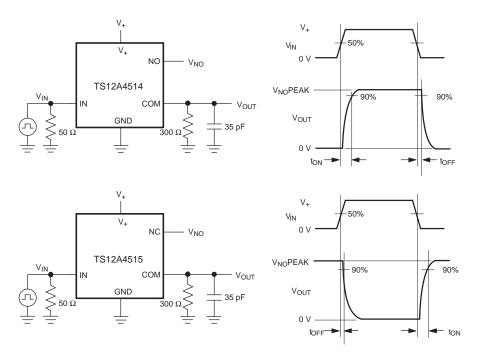


Figure 2. Switching Times

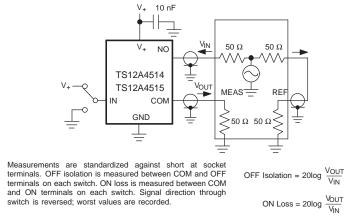


Figure 3. OFF Isolation and ON Loss

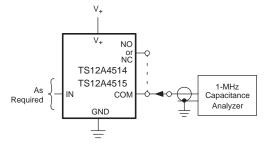


Figure 4. NO, NC, and COM Capacitance

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PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package | Pine | Package | Eco Plan | Lead finish/ | MSL Peak Temp | Op Temp (°C) | Device Marking | Samples |
|------------------|---------|---------------|---------|------|---------|--------------|---------------|--------------------|--------------|----------------|---------|
| Gradiable Bevice | (1) | r dokage Type | Drawing | | Qty | (2) | Ball material | (3) | op remp (o) | (4/5) | Campies |
| | (1) | | J | | , | (2) | (6) | (0) | | (40) | |
| TS12A4514D | ACTIVE | SOIC | D | 8 | 75 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | YD514 | Samples |
| TS12A4514DBVR | ACTIVE | SOT-23 | DBV | 5 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 9CJE | Samples |
| TS12A4514DR | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | YD514 | Samples |
| TS12A4514P | LIFEBUY | PDIP | Р | 8 | 50 | RoHS & Green | NIPDAU | N / A for Pkg Type | -40 to 85 | TS12A4514P | |
| TS12A4515D | ACTIVE | SOIC | D | 8 | 75 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | YD515 | Samples |
| TS12A4515DBVR | ACTIVE | SOT-23 | DBV | 5 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | 9CKE | Samples |
| TS12A4515DR | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | YD515 | Samples |
| TS12A4515DRG4 | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | YD515 | Samples |
| TS12A4515P | LIFEBUY | PDIP | Р | 8 | 50 | RoHS & Green | NIPDAU | N / A for Pkg Type | -40 to 85 | TS12A4515P | |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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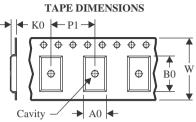
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





| | - |
|----|---|
| A0 | Dimension designed to accommodate the component width |
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---------------|-----------------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TS12A4514DBVR | SOT-23 | DBV | 5 | 3000 | 179.0 | 8.4 | 3.2 | 3.2 | 1.4 | 4.0 | 8.0 | Q3 |
| TS12A4514DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| TS12A4515DBVR | SOT-23 | DBV | 5 | 3000 | 179.0 | 8.4 | 3.2 | 3.2 | 1.4 | 4.0 | 8.0 | Q3 |
| TS12A4515DR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

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*All dimensions are nominal

| 7 III GIITTOTTOTOTTO GITO TTOTTIII | | | | | | | |
|------------------------------------|--------------|-----------------|------|------|-------------|------------|-------------|
| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| TS12A4514DBVR | SOT-23 | DBV | 5 | 3000 | 200.0 | 183.0 | 25.0 |
| TS12A4514DR | SOIC | D | 8 | 2500 | 356.0 | 356.0 | 35.0 |
| TS12A4515DBVR | SOT-23 | DBV | 5 | 3000 | 200.0 | 183.0 | 25.0 |
| TS12A4515DR | SOIC | D | 8 | 2500 | 356.0 | 356.0 | 35.0 |

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| TS12A4514D | D | SOIC | 8 | 75 | 506.6 | 8 | 3940 | 4.32 |
| TS12A4514P | Р | PDIP | 8 | 50 | 506 | 13.97 | 11230 | 4.32 |
| TS12A4515D | D | SOIC | 8 | 75 | 506.6 | 8 | 3940 | 4.32 |
| TS12A4515P | Р | PDIP | 8 | 50 | 506 | 13.97 | 11230 | 4.32 |



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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